

Title (en)
HETEROJUNCTION TRANSISTOR WITH VERTICAL STRUCTURE

Title (de)
HETEROÜBERGANGSTRANSISTOR MIT VERTIKALER STRUKTUR

Title (fr)
TRANSISTOR À HÉTÉROJONCTION À STRUCTURE VERTICALE

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Application
EP 17804252 A 20171114

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Abstract (en)
[origin: WO2018100262A1] The invention concerns a heterojunction field-effect transistor (1) comprising: - a stack of first and second III-N type semiconducting layers (14, 13) forming an electron gas or hole layer (15); - a first conduction electrode (21) in electrical contact with the gas layer and a second conduction electrode (22); - a separation layer (12) positioned vertically in line with the first electrode and under the second semiconducting layer (13); - a third semiconducting layer (11) arranged under the separation layer (12) and in electrical contact with the second electrode; - a conductive element (24) in electrical contact with the gas layer (15) and electrically connecting the third semiconducting layer (11) and the gas layer (15); and - a control gate (23) positioned between the conductive element (24) and the first conduction electrode (21).

IPC 8 full level
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